

**[ABSTRACT]****[Abstract of the Disclosure]**

The present invention relates to a phase edge phase shift mask and a fabrication method thereof enforcing width of a field gate image located on a field region, which gets  
5 weak owing to two exposure processes, by using a phase shift mask and a trim mask on a semiconductor substrate, and enforcing width of the field gate image in order to maximize a current driving capability of the semiconductor device accordingly.

**[Representative Drawing]**

10 Fig. 2A